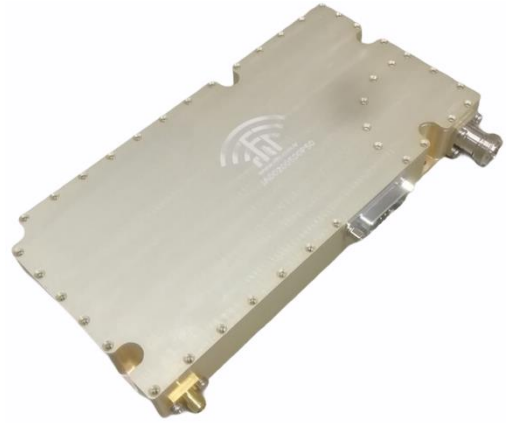


JA00200500P49; 20-500 MHz 80W

- Solid-state Class AB design
- MOS Transistors
- High reliability and ruggedness
- Ultra Broadband
- Temperature and Current Monitorings
- Forward & Reflected Power Monitorings



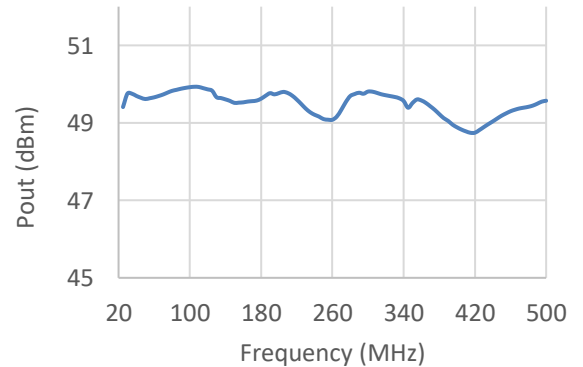
ELECTRICAL & ENVIRONMENTAL SPECIFICATIONS

Frequency:	20-500 MHz
Output Power:	80 W CW
Nominal Gain:	49 dB
Gain Flatness:	± 2.0 dB
Input VSWR:	2:1 max.
Load VSWR for Survival:	∞:1 for 1min.
DC Supply Voltage:	28 V
DC Current:	8.5 A Avg
Operating Case Temp.:	-40 °C to 85 °C
Storage Temperature:	-40 °C to 85 °C
Shock:	MIL-STD-810F, 516.5
Vibration:	MIL-STD-810F, 514.5

INTERFACES

RF Input:	SMA Female
RF Output:	N Female
9 PIN DSUB:	1) Enable (Active Low)
	2) GND
	3) Temp.
	4) Fwd. Power
	5) Rev. Power
	A1) GND
	A2) 28 V

Typical Pout vs Frequency @ Pin=0 dBm



MECHANICAL SPECIFICATIONS

Size (mm) :	97 x 194 x 24
Weight :	600 gr.
Plating :	Yellow Chromate

